

# Holographic charge localization at brane intersections

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MAX-PLANCK-GESELLSCHAFT



Max-Planck-Institut für Physik  
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- Background: charge density  $\rho(x)$
- Fluctuations: Conductivities  $\sigma_y(x)$ ,  $\sigma_x(x)$

## 3 Conclusions and Outlook

## PROBE BRANES

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$D_p/D_q$  intersections with charge density and chemical potential.

- [hep-th/0611099]

Kobayashi, Mateos, Matsuura, Myers, Thomson

- [0709.1225]

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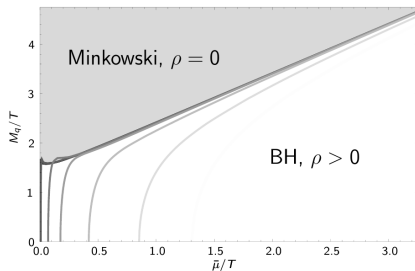
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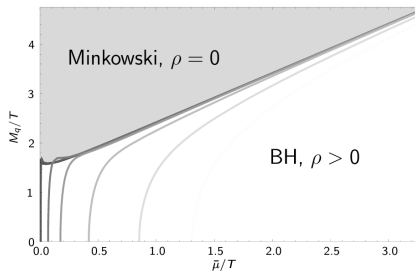
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### Important

- + "Minkowski" or "BH".
- + Minkowski above given  $M$ .
- +  $\rho \neq 0 \Rightarrow$  only BH are possible.
- +  $\rho, M > 0$ : BH above given  $\mu$ .

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D<sub>3</sub>/D<sub>7</sub> to holographically realize TI via  $m(x)$

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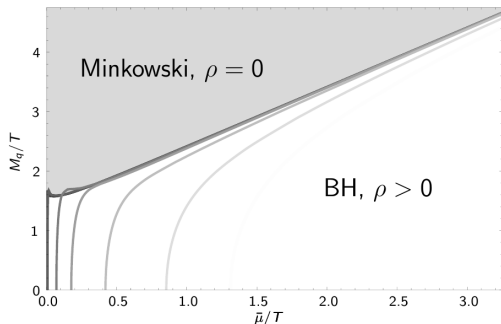
### Key idea

$m$  function of spatial coordinate

$$m(x) = M \left( \frac{2}{1 + e^{-ax}} - 1 \right)$$

$$m(\pm\infty) \rightarrow \pm M \quad m(0) = 0$$

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## Set-up

Geometry generated by stack of black D3-branes

$$ds^2 = \frac{L^2}{z^2} \left( -\frac{f(z)^2}{h(z)} dt^2 + h(z) d\vec{x}^2 + dz^2 \right) + L^2 d\Omega_5^2$$

with

$$f(z) = 1 - \frac{z^4}{z_0^4} \quad h(z) = 1 + \frac{z^4}{z_0^4}$$

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Embed D5-brane

	$t$	$x$	$y$	$v$	$z$	$\Omega_2$	$\tilde{\Omega}_2$	$\theta$
D3	×	×	×	×				
D5	×	×	×		×	×		

$$d\Omega_5^2 = d\theta^2 + \sin^2 \theta d\Omega_2^2 + \cos^2 \theta d\tilde{\Omega}_2^2$$

$$\cos \theta = \chi$$

# Background

Embedding is determined by

$$A = \phi(z, x)dt \quad \chi(z, x)$$

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IR behaviour (regularity)

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## Resolution of the background

Numerical resolution of EOMs: Chebyshev + Newton-Raphson

$$\phi(1, x) = 0, \quad \chi'(1, x) = 0$$

$$\chi'(0, x) = M \left( \frac{2}{1 + e^{-ax}} - 1 \right) \quad \phi(0, x) = \mu$$

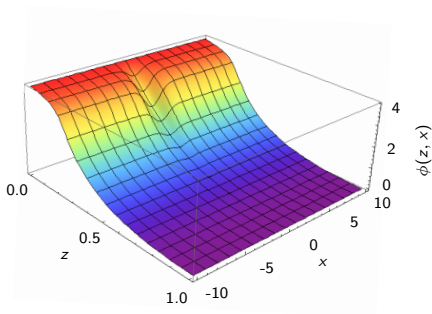
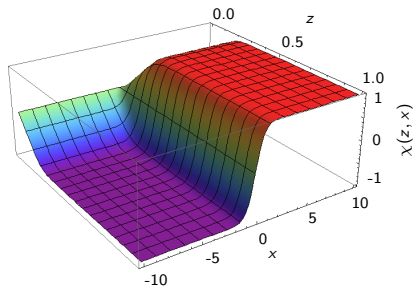


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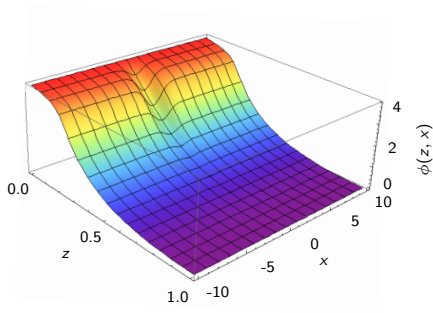
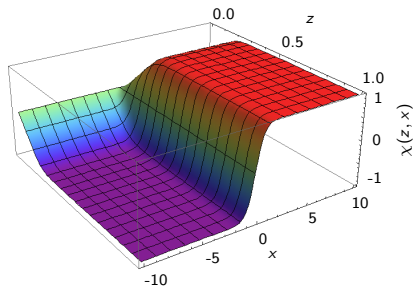


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$$\dot{\chi}(z, \pm L) = 0, \quad \dot{\phi}(z, \pm L) = 0$$

## Results for background

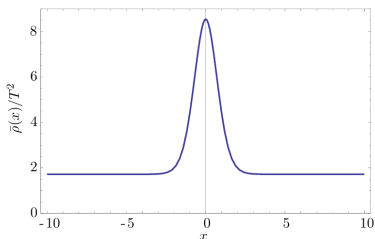
Can read charge density

$$\rho(x) = -\partial_z \phi(z, x)|_{z=0}$$

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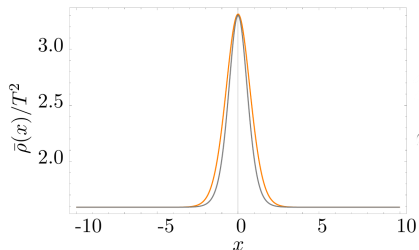
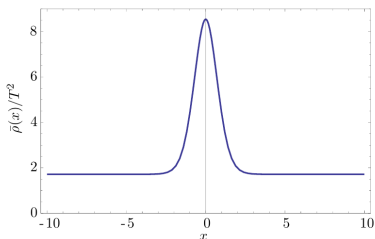
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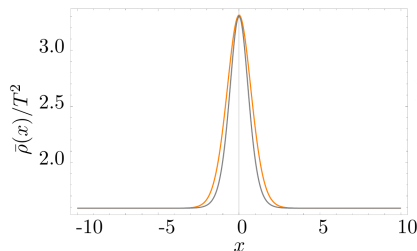
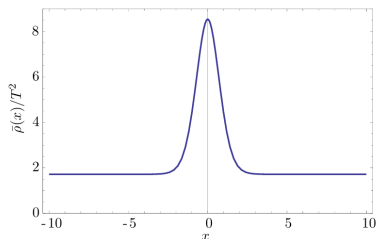
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## Results

- D3/D5 intersection realises (1+1)-dim interface.
- $\rho(x)$  is localised at the interface.
- Enhancement bigger close to phase transition.
- Not exactly as for homogeneous case.



# Fluctuations

Study linear response to electric field to analyse conductivities.

$$A_\mu = A_\mu(z, x) + a_\mu(z, x)e^{i\omega t}$$

$$\chi = \chi(z, x) + c(z, x)e^{i\omega t}$$

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→ 3 linear PDEs + constraint
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$f_{ti} = (i\omega \epsilon_i) e^{i\omega t}$	$\sigma_i(\omega, x) = \frac{j_i}{i\omega \epsilon_i} = \frac{f_{iz}}{f_{ti}} \Big _{z=0}$	$(i = x, y)$
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IR: infalling wave condition

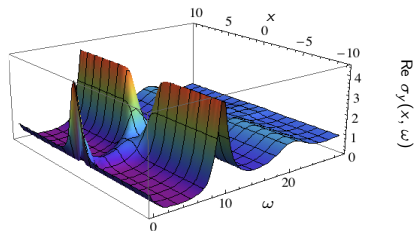
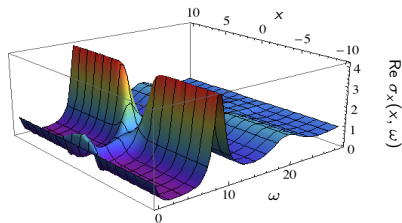
UV: no mass fluctuations +  
homogeneous E + constraint

# Conductivities

Use same numerical apparatus as for background.

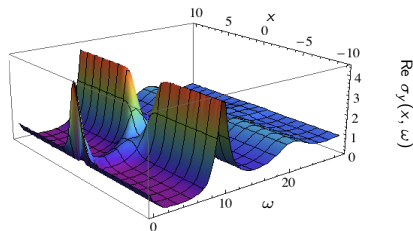
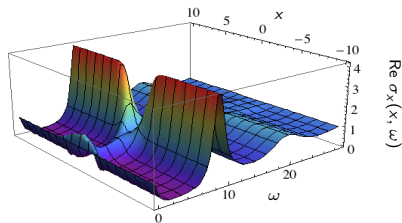
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## Results

- $\sigma_x$  and  $\sigma_y$  look alike at high  $\omega$  and away from interface.
- $\sigma_x$  and  $\sigma_y$  differ at low  $\omega$  and close to interface.
- $\sigma_x$  is suppressed (feels charge density all over (mostly edges)).
- $\sigma_y$  is enhanced (feels charge density at interface).

# DC conductivity $\sigma_x^{DC}$

Can do the same as in

- [0809.3808] Iqbal, Liu
- [1103.6068] Ryu, Takayanagi, Ugajin

EOMs in DC limit ( $\omega \rightarrow 0$ )

$$d\zeta = \sqrt{h(z)/f(z)^2} dz$$

$$\partial_\zeta (\mathcal{F}(\zeta, x) \partial_\zeta \mathbf{a}_x) = 0$$

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Constant expression

$$\sigma_x^{DC} = \mathcal{F}(z=1, x) \left(1 + \partial_x \frac{\mathbf{a}_t(0, x)}{i\omega}\right)$$



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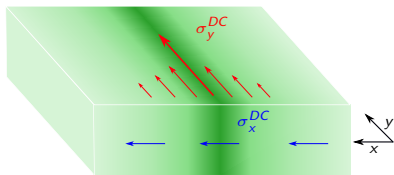
$$\sigma_x^{DC} = \mathcal{F}(z=1, x) \left(1 + \partial_x \frac{\mathbf{a}_t(0, x)}{i\omega}\right)$$

$\sigma_x^{DC}$  from IR data

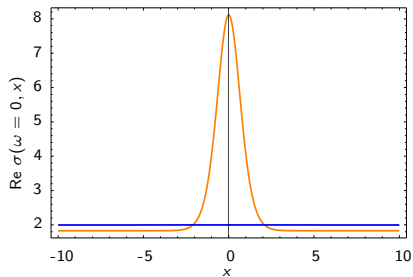
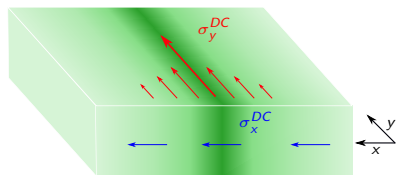
$$\sigma_x^{DC} = \frac{2L}{\int_{-L}^L \frac{dx}{\mathcal{F}(1, x)}},$$

Short vs long systems  $\rightarrow$  different BCs

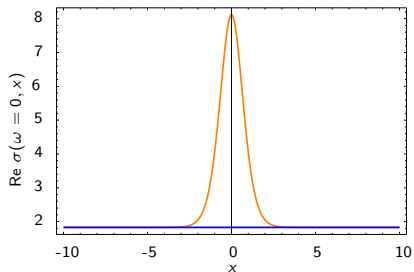
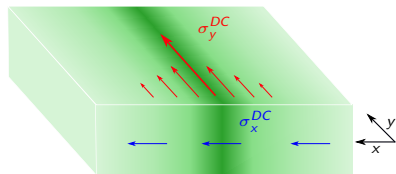
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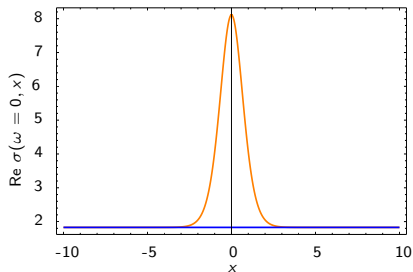
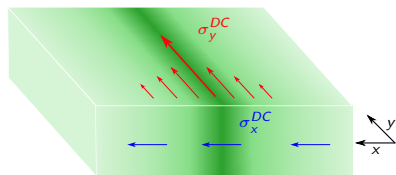
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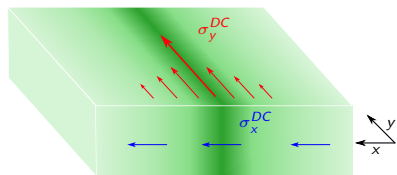


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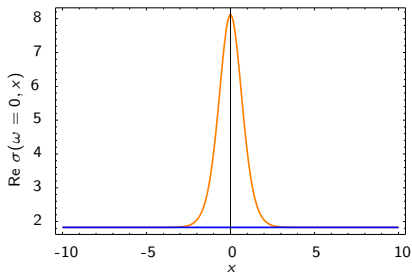
$\sigma_x^{DC}$  sensible to system size

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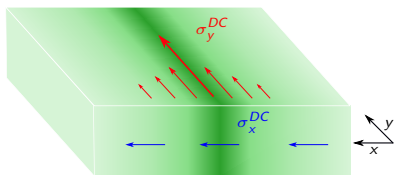
$\sigma_y^{DC}$  is also sensitive to inhomogeneity.

- Gradients in  $\chi$  and  $\phi$ :  $\rho(x)$
- Fluctuation EOMs



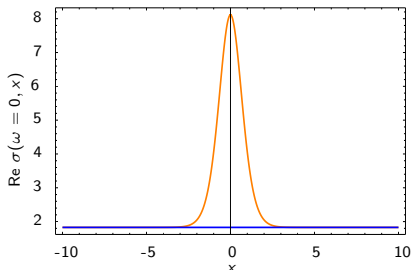
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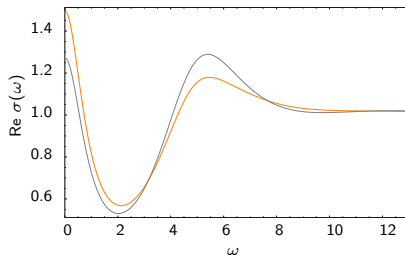


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$\sigma_x^{DC}$  sensitive to system size



Mostly due to  $\rho(x)$ .  
Sensitive to system size.

# Conclusions and Outlook

## CONCLUSIONS

- D3/D5 intersection in probe limit realises 1-dim charged interface.
- Charge density peaks at interface ( $\rho_0 \sim 5\rho_L$ ).
- $\sigma_x(\omega, x) \sim \sigma_y(\omega, x)$  at  $\omega, x \gg 0$ .  $\sigma_x(\omega, x) \neq \sigma_y(\omega, x)$  at  $\omega, x \rightarrow 0$
- $\sigma_y(\omega, x)$  sensitive to  $\partial_x$ .
- Current conservation: constant  $\sigma_x^{DC}$ . IR background data.
  - +  $\sigma_x^{DC} \leftrightarrow \rho_L$ ,  $\sigma_y^{DC} \leftrightarrow \rho(x)$ .
  - + At  $x = 0$ ,  $\sigma_y^{DC} \sim 4\sigma_x^{DC}$ .
- Sensible to system length.  $\rho(x)$  overpowers  $\partial_x\rho(x)$



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## FUTURE DIRECTIONS

- Turn on topological terms.
- Look for signatures of Fermi surface.
- Study effects of disorder.